

DS34LV87T Enhanced CMOS Quad Differential Line Driver

Check for Samples: [DS34LV87T](#)

FEATURES

- Meets TIA/EIA-422-B (RS-422) and ITU-T V.11 Recommendation
- Interoperable With Existing 5V RS-422 Networks
- Ensured V_{OD} of 2V Min Over Operating Conditions
- Balanced Output Crossover for Low EMI (Typical Within 40 mV of 50% Voltage Level)
- Low Power Design (330 μ W @ 3.3V Static)
- ESD ≥ 7 kV on Cable I/O Pins (HBM)
- Industrial Temperature Range
- Ensured AC Parameter:
 - Maximum Driver Skew: 2 ns
 - Maximum Transition Time: 10 ns
- Pin Compatible With DS26C31
- Available in SOIC Packaging

DESCRIPTION

The DS34LV87T is a high speed quad differential CMOS driver that meets the requirements of both TIA/EIA-422-B and ITU-T V.11. The CMOS DS34LV87T features low static I_{CC} of 100 μ A max which makes it ideal for battery powered and power conscious applications. The TRI-STATE enable, EN, allows the device to be disabled when the device is not in use to minimize power. The dual enable scheme allows for flexibility in turning devices on or off.

Protection diodes protect all the driver inputs against electrostatic discharge. The driver and enable inputs (DI and EN) are compatible with LVTTTL and LVC MOS devices. Differential outputs have the same V_{OD} (≥ 2 V) ensure as the 5V version. The outputs have enhanced ESD Protection providing greater than 7 kV tolerance.

Connection Diagram

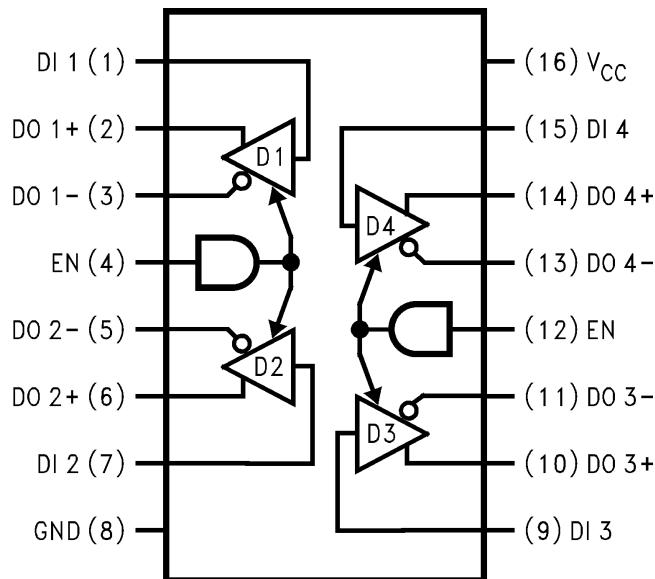


Figure 1. Dual-In-Line Package (Top View)
See Package Number D0016A

TRUTH TABLE⁽¹⁾

Enables	Input	Outputs	
EN	DI	DO+	DO-
L	X	Z	Z
H	H	H	L
H	L	L	H

- (1) L = Low logic state
X = Irrelevant
H = High logic state
Z = TRI-STATE



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ABSOLUTE MAXIMUM RATINGS⁽¹⁾⁽²⁾

Supply Voltage (V_{CC})		-0.5V to +7V
Enable Input Voltage (EN)		-0.5V to $V_{CC} + 0.5V$
Driver Input Voltage (D_I)		-0.5V to $V_{CC} + 0.5V$
Clamp Diode Current		± 20 mA
DC Output Current, per pin		± 150 mA
Driver Output Voltage	(Power Off: DO+, DO-)	-0.5V to +7V
Maximum Package Power Dissipation @+25°C	D Package	1226 mW
Derate D Package		9.8 mW/°C above +25°C
Storage Temperature Range		-65°C to +150°C
Lead Temperature Range (Soldering, 4 sec.)		+260°C
ESD Ratings (HBM, 1.5k, 100 pF)	Driver Outputs	≥ 7 kV
	Other Pins	≥ 2.5 kV

- (1) If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/ Distributors for availability and specifications.
- (2) Absolute Maximum Ratings are those values beyond which the safety of the device cannot be ensured. They are not meant to imply that the device should be operated at these limits. The table of [Electrical Characteristics](#) specifies conditions of device operation.

RECOMMENDED OPERATING CONDITIONS

		Min	Typ	Max	Units
Supply Voltage (V_{CC})		3.0	3.3	3.6	V
Operating Free Air	Temperature Range (T_A) DS34LV87T	-40	25	+85	°C
Input Rise and Fall Time				500	ns

ELECTRICAL CHARACTERISTICS⁽¹⁾⁽²⁾

Over Supply Voltage and Operating Temperature ranges, unless otherwise specified

Symbol	Parameter	Conditions	Pin	Min	Typ	Max	Units
V _{OD1}	Output Differential Voltage	R _L = ∞, (No Load)	DO+, DO–		3.3	4.0	V
V _{OD2}	Output Differential Voltage	R _L = 100Ω See Figure 2		2	2.6		V
ΔV _{OD2}	Change in Magnitude of Output Differential Voltage			–400	7	400	mV
V _{OD3}	Output Differential Voltage	R _L = 3900Ω (V.11), See Figure 2 ⁽³⁾			3.2	3.5	V
V _{OC}	Common Mode Voltage	R _L = 100Ω See Figure 2			1.5	2	V
ΔV _{OC}	Change in Magnitude of Common Mode Voltage			–400	6	400	mV
I _{OZ}	TRI-STATE Leakage Current	V _{OUT} = V _{CC} or GND Drivers Disabled			±0.5	±20	μA
I _{SC}	Output Short Circuit Current	V _{OUT} = 0V V _{IN} = V _{CC} or GND ⁽⁴⁾		–40	–70	–150	mA
I _{OFF}	Output Leakage Current	V _{CC} = 0V, V _{OUT} = 3V			0.03	100	μA
		V _{CC} = 0V, V _{OUT} = –0.25V			–0.08	–100	μA
V _{IH}	High Level Input Voltage		DI, EN	2.0		V _{CC}	V
V _{IL}	Low Level Input Voltage			GND		0.8	V
I _{IH}	High Level Input Current	V _{IN} = V _{CC}				10	μA
I _{IL}	Low Level Input Current	V _{IN} = GND		–10			μA
V _{CL}	Input Clamp Voltage	I _{IN} = –18 mA				–1.5	V
I _{CC}	Power Supply Current	No Load, V _{IN} (all) = V _{CC} or GND	V _{CC}			100	μA

- (1) Current into device pins is defined as positive. Current out of device pins is defined as negative. All voltages are referenced to ground except differential voltages V_{OD1}, V_{OD2}, V_{OD3}.
- (2) All typical values are given for V_{CC} = 3.3V and T_A = +25°C.
- (3) This specification limit is for compliance with TIA/EIA-422-B and ITU-T V.11.
- (4) Only one output shorted at a time. The output (true or complement) is configured High.

SWITCHING CHARACTERISTICS⁽¹⁾⁽²⁾

Over Supply Voltage and Operating Temperature ranges, unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Units
t_{PHLD}	Differential Propagation Delay High to Low	$R_L = 100\Omega$, $C_L = 50\text{ pF}$ See Figure 3 and Figure 4	6	10.5	16	ns
t_{PLHD}	Differential Propagation Delay Low to High		6	11	16	ns
t_{SKD}	Differential Skew $ t_{PHLD} - t_{PLHD} $			0.5	2.0	ns
t_{SK1}	Skew, Pin to Pin (same device)			1.0	2.0	ns
t_{SK2}	Skew, Part to Part ⁽³⁾			3.0	5.0	ns
t_{TLH}	Differential Transition Time Low to High (20% to 80%)			4.2	10	ns
t_{THL}	Differential Transition Time High to Low (80% to 20%)			4.7	10	ns
t_{PHZ}	Disable Time High to Z	See Figure 5 and Figure 6		12	20	ns
t_{PLZ}	Disable Time Low to Z			9	20	ns
t_{PZH}	Enable Time Z to High			22	32	ns
t_{PZL}	Enable Time Z to Low			22	32	ns
f_{MAX}	Maximum Operating Frequency ⁽⁴⁾			32		MHz

(1) $f = 1\text{ MHz}$, t_r and $t_f \leq 6\text{ ns}$ (10% to 90%).

(2) See TIA/EIA-422-B specifications for exact test conditions.

(3) Devices are at the same V_{CC} and within 5°C within the operating temperature range.

(4) All channels switching, output duty cycle criteria is 40%/60% measured at 50%. This parameter is ensured by design and characterization.

PARAMETER MEASUREMENT INFORMATION

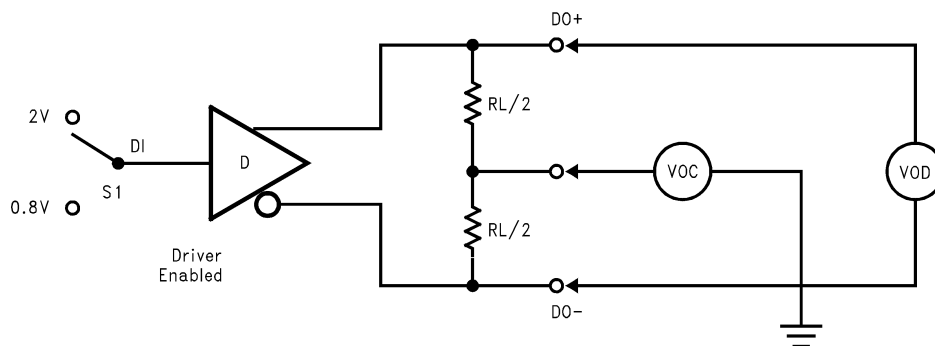


Figure 2. Differential Driver DC Test Circuit

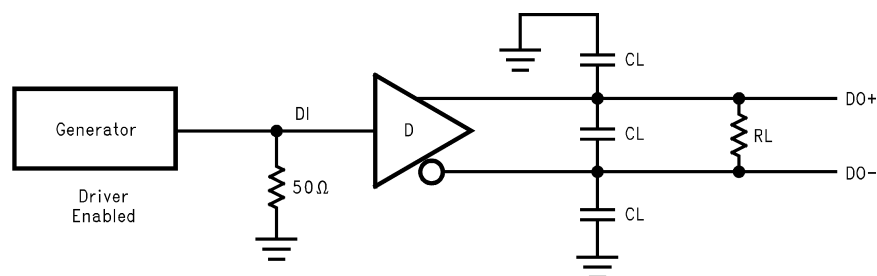
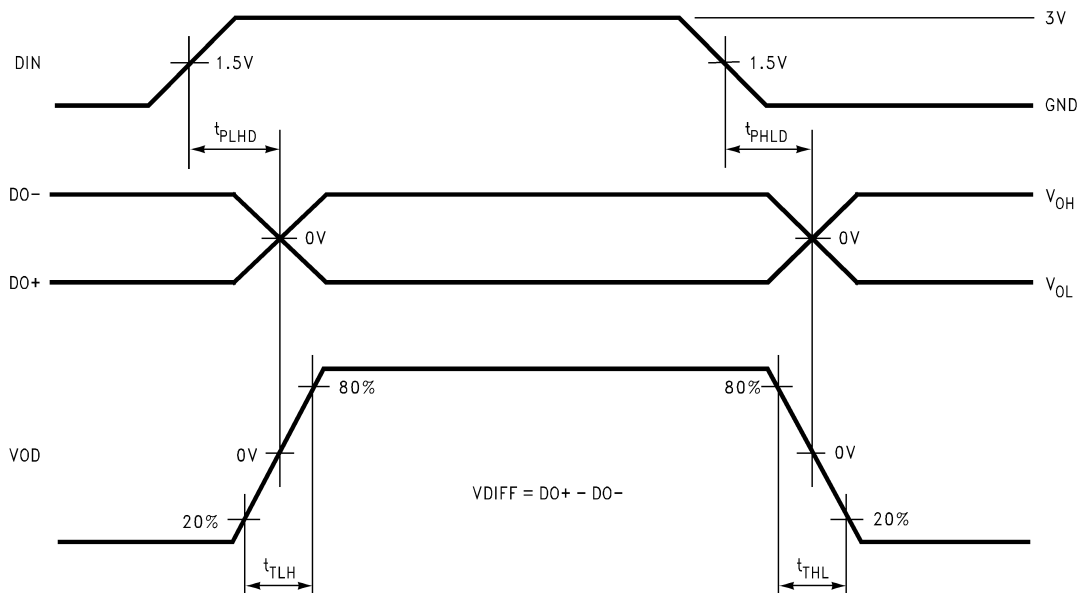


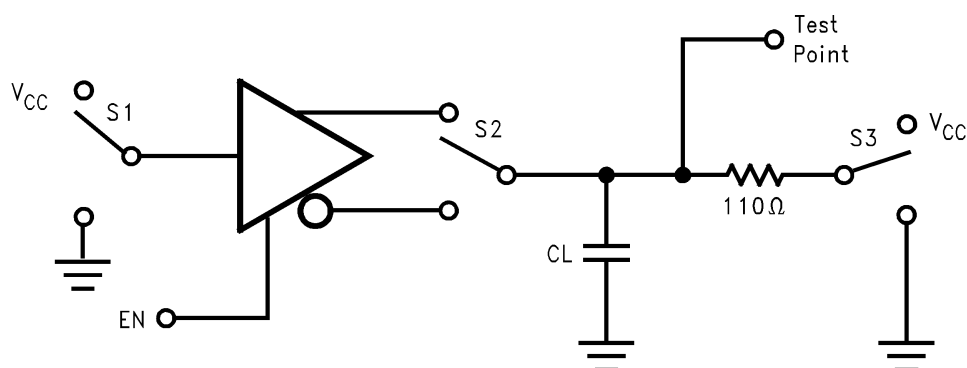
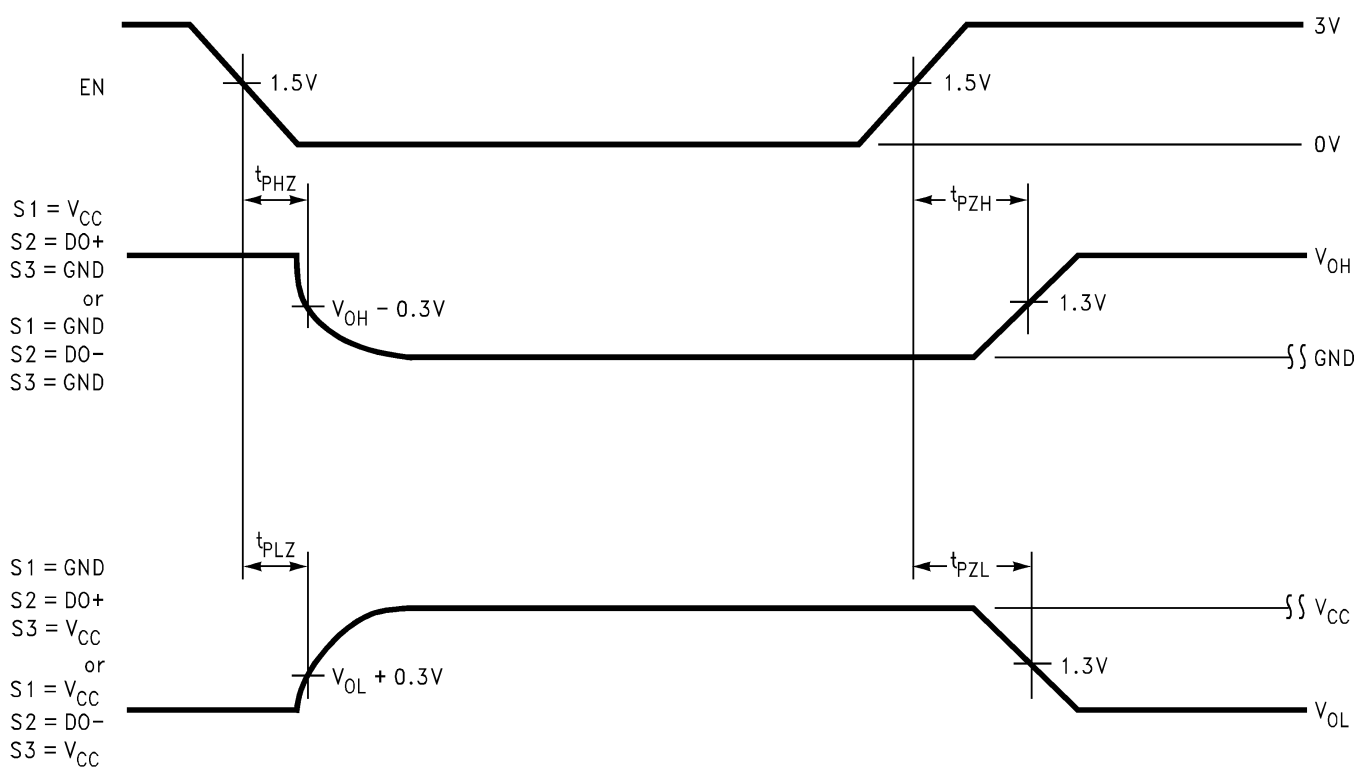
Figure 3. Differential Driver Propagation Delay and Transition Time Test Circuit



Generator waveform for all tests unless otherwise specified: $f = 1 \text{ MHz}$, Duty Cycle = 50%, $Z_0 = 50\Omega$, $t_r \leq 10 \text{ ns}$, $t_f \leq 10 \text{ ns}$.

C_L includes probe and fixture capacitance.

Figure 4. Differential Driver Propagation Delay and Transition Time Waveforms

PARAMETER MEASUREMENT INFORMATION (continued)**Figure 5. Driver Single-Ended Tri-state Test Circuit****Figure 6. Driver Single-Ended Tri-state Waveforms**

TYPICAL APPLICATION INFORMATION

General application guidelines and hints for differential drivers and receivers may be found in the following application notes:

- Transmission Line Drivers and Receivers for TIA/EIA Standards RS-422 and RS-423([SNLA137](#))
- A Comparison of Differential Termination Techniques([SNLA304](#))

Power Decoupling Recommendations:

Bypass caps must be used on power pins. High frequency ceramic (surface mount is recommended) 0.1 μF in parallel with 0.01 μF at the power supply pin. A 10 μF or greater tantalum or electrolytic should be connected at the power entry point on the printed circuit board.

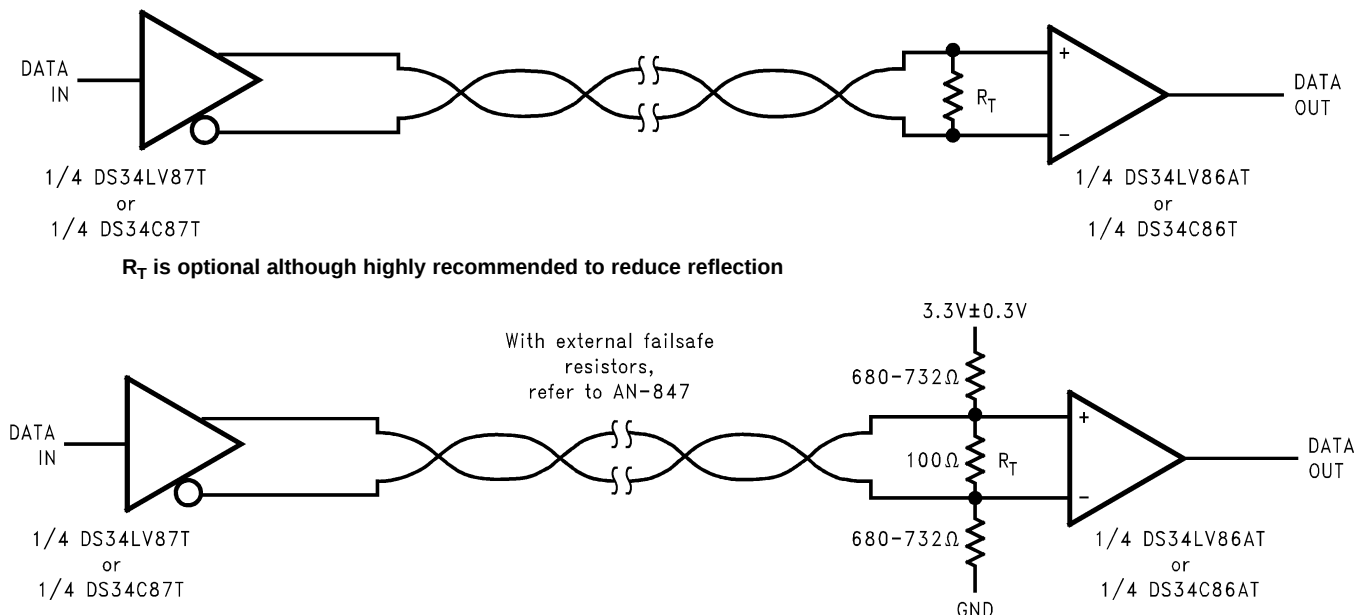


Figure 7. Typical Driver Connection

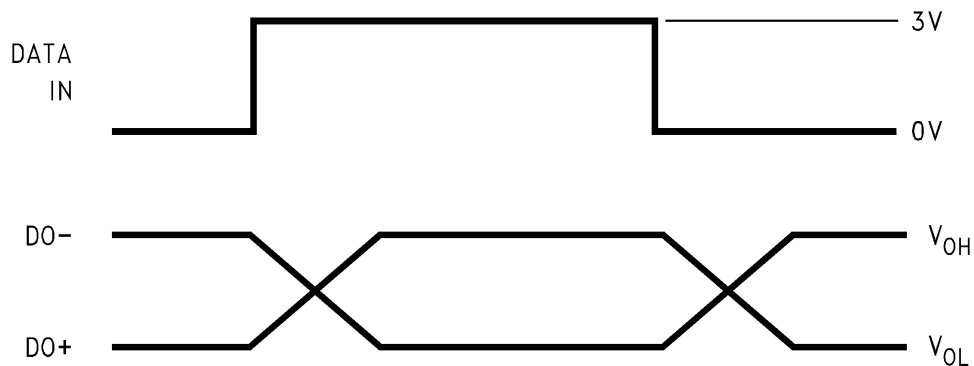


Figure 8. Typical Driver Output Waveforms

REVISION HISTORY

Changes from Revision C (April 2013) to Revision D

Page

- Changed layout of National Data Sheet to TI format [7](#)

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
DS34LV87TM/NOPB	ACTIVE	SOIC	D	16	48	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	DS34LV87 TM	Samples
DS34LV87TMX/NOPB	ACTIVE	SOIC	D	16	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	DS34LV87 TM	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

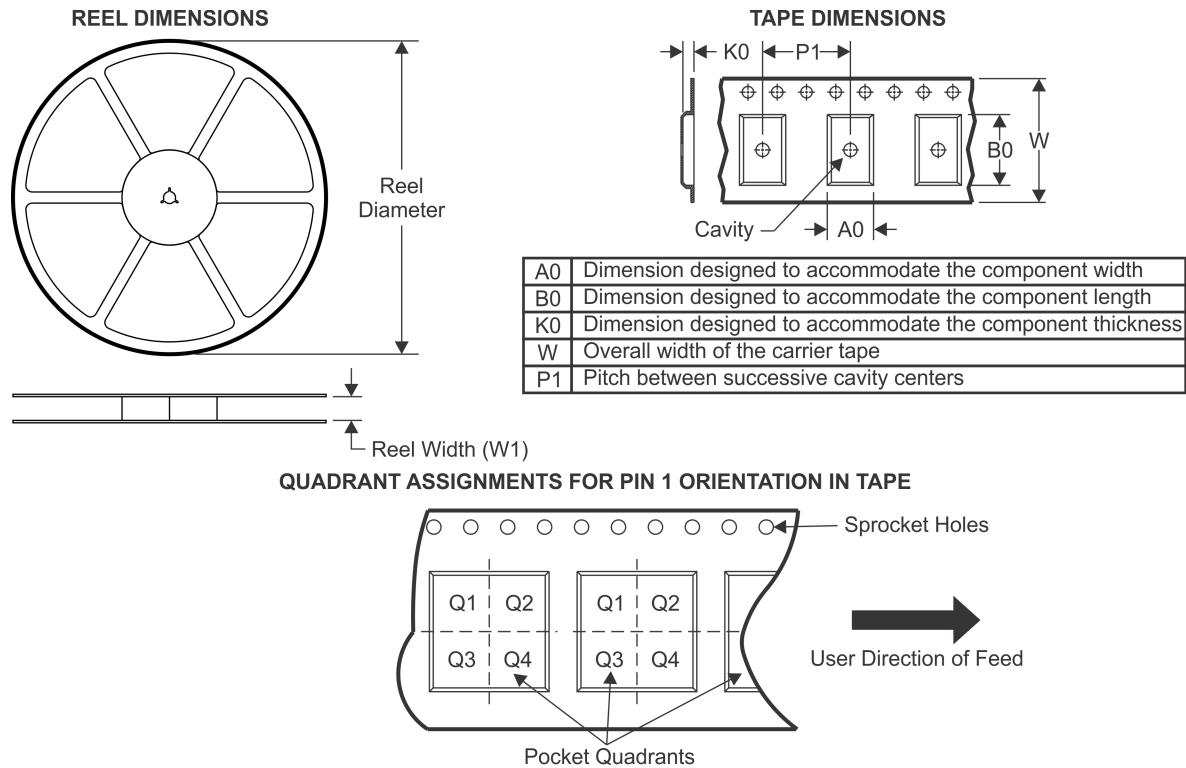
(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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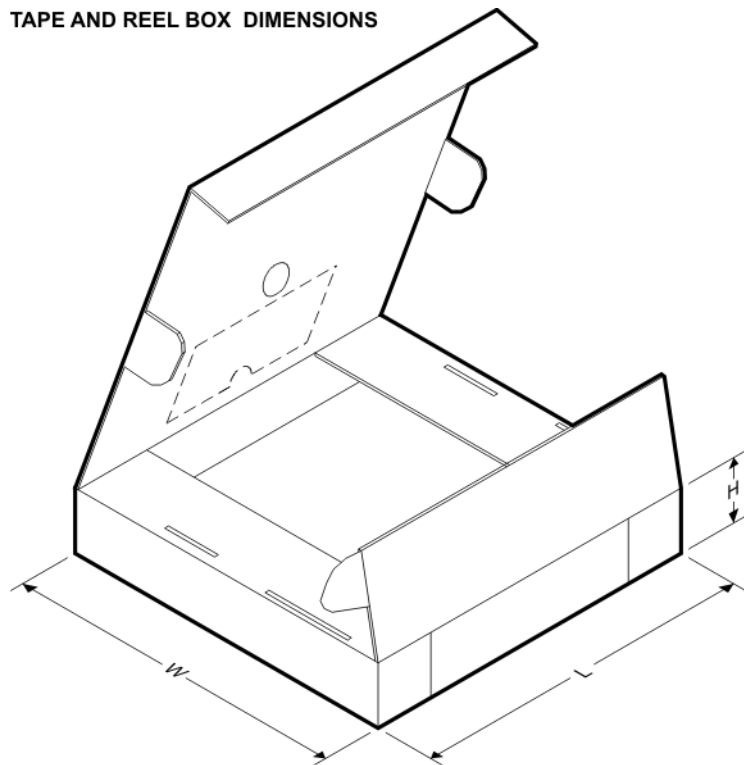
TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DS34LV87TMX/NOPB	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.3	8.0	16.0	Q1

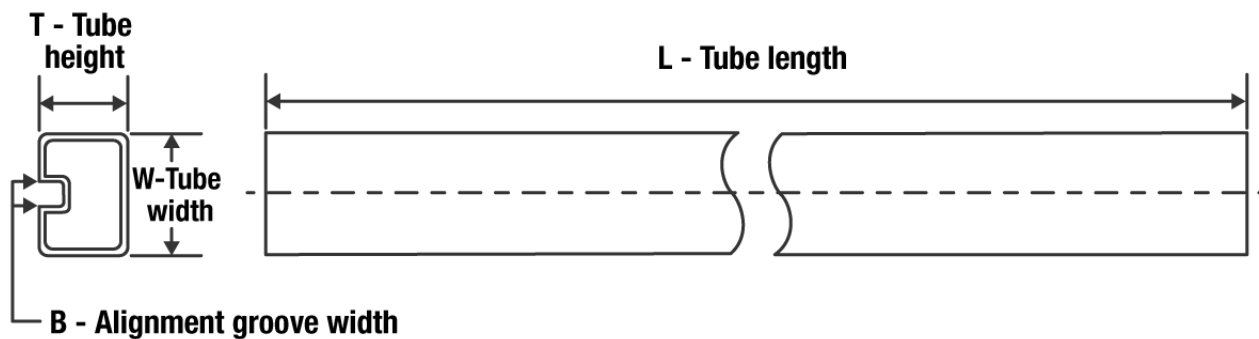
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DS34LV87TMX/NOPB	SOIC	D	16	2500	356.0	356.0	35.0

TUBE

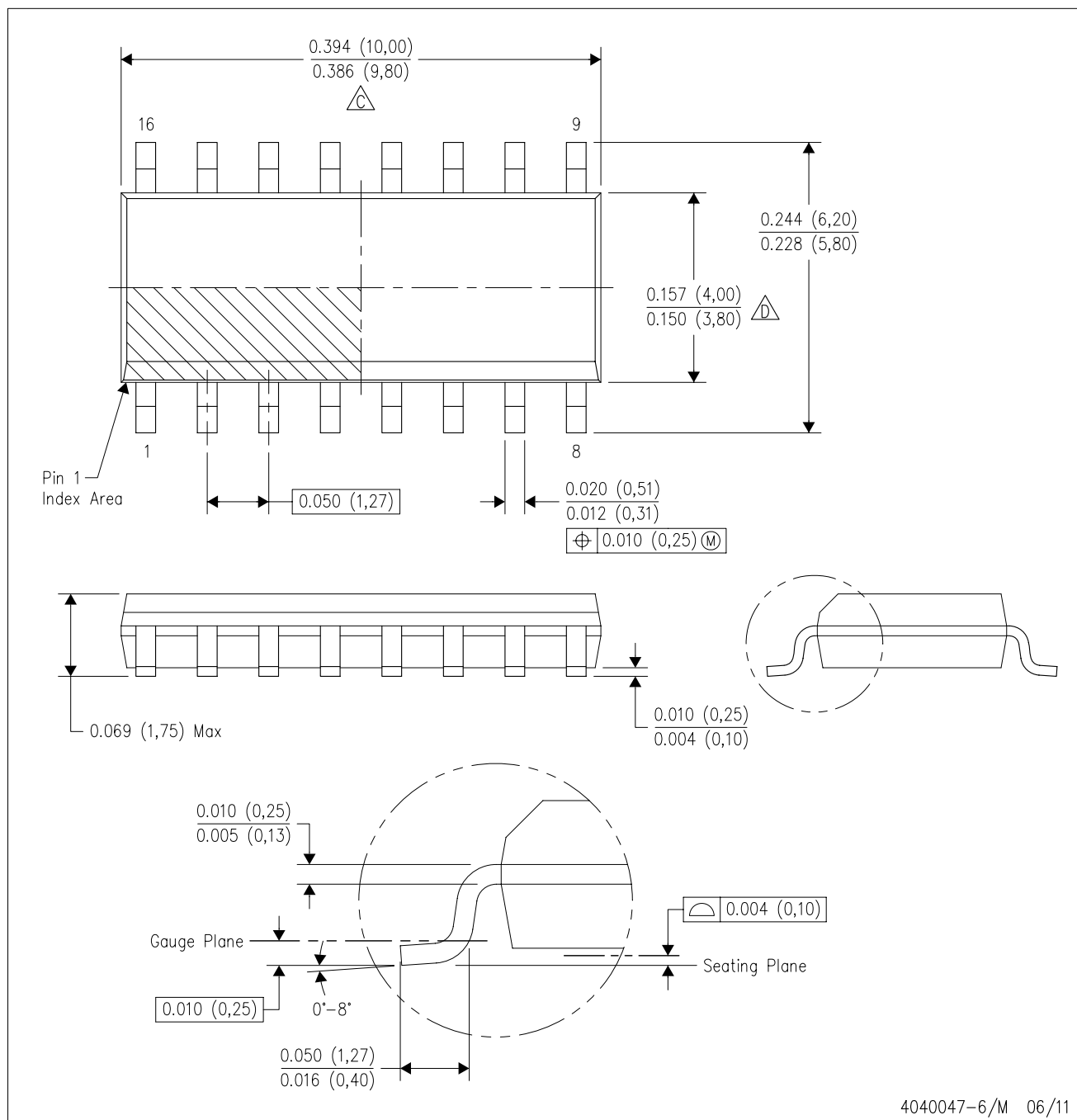


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (μm)	B (mm)
DS34LV87TM/NOPB	D	SOIC	16	48	495	8	4064	3.05

D (R-PDSO-G16)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- $\triangle C$ Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- $\triangle D$ Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.

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